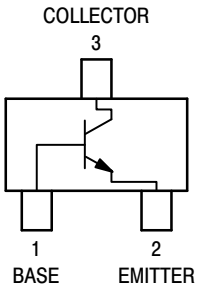
NPN General Purpose Amplifier Transistors Surface Mount

MSD601-RT1G, NSVMSD601-RT1G



Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25 °C)

Rating	Symbol	Value	Unit
Collector – Base Voltage	$V_{(BR)CBO}$	60	Vdc
Collector – Emitter Voltage	$V_{(BR)CEO}$	50	Vdc
Emitter – Base Voltage	$V_{(BR)EBO}$	7.0	Vdc
Collector Current – Continuous	I_C	100	mAdc
Collector Current – Peak	$I_{C(P)}$	200	mAdc

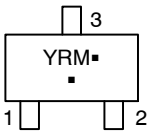
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Power Dissipation	P_D	200	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	−55 ~ +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

SC-59
CASE 318D

MARKING DIAGRAM



YR = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

Characteristic	Symbol	Min	Max	Unit
Collector – Emitter Breakdown Voltage (I_C = 2.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	50		Vdc
Collector – Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	60		Vdc
Emitter – Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	7.0		Vdc
Collector – Base Cutoff Current (V_{CB} = 45 Vdc, I_E = 0)	I_{CBO}		0.1	μAdc
Collector – Emitter Cutoff Current (V_{CE} = 10 Vdc, I_B = 0)	I_{CEO}		100	nAdc
DC Current Gain (Note 1) (V_{CE} = 10 Vdc, I_C = 2.0 mAdc) (V_{CE} = 2.0 Vdc, I_C = 100 mAdc)	h_{FE1} h_{FE2}	210 90	340	–
Collector – Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 10 mAdc)	$V_{CE(sat)}$		0.5	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width ≤ 300 μs, D.C. ≤ 2%.

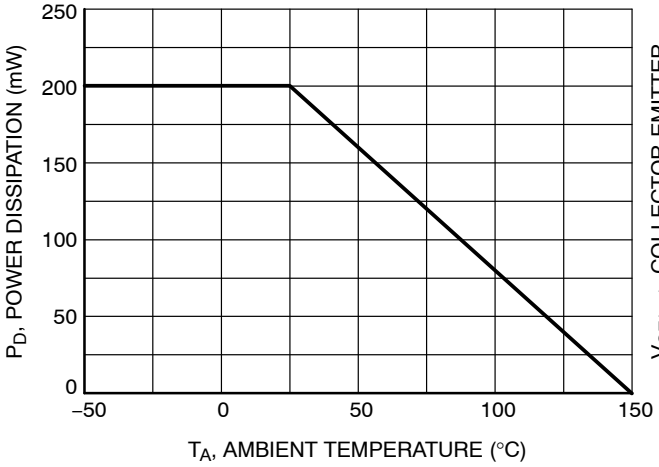

Figure 1. Derating Curve

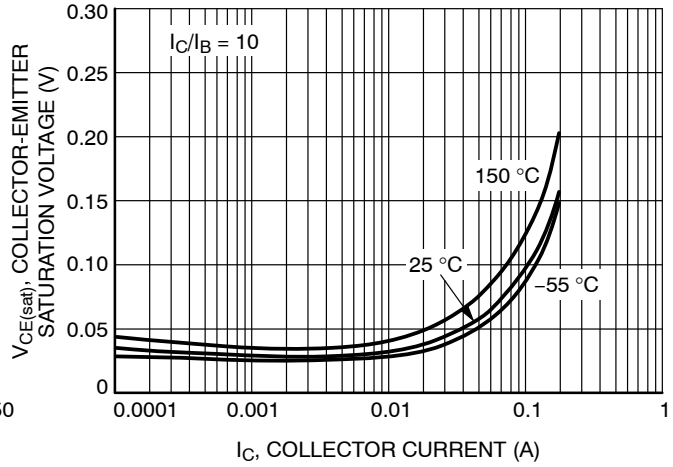

Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

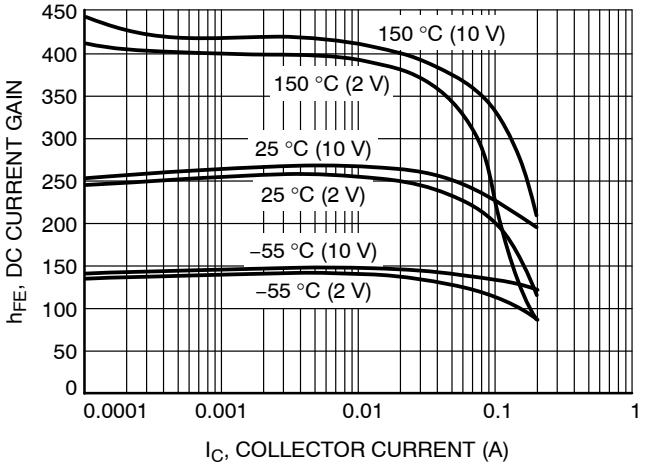

Figure 3. DC Current Gain vs. Collector Current

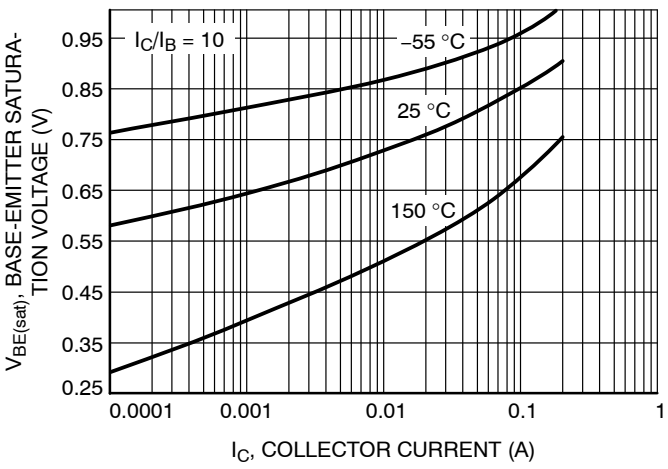

Figure 4. Base Emitter Saturation Voltage vs. Collector Current

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TYPICAL CHARACTERISTICS

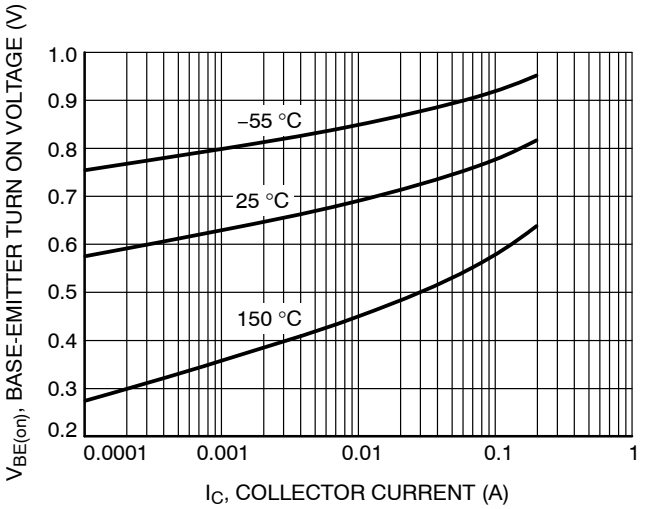

Figure 5. Base Emitter Turn-On Voltage vs. Collector Current

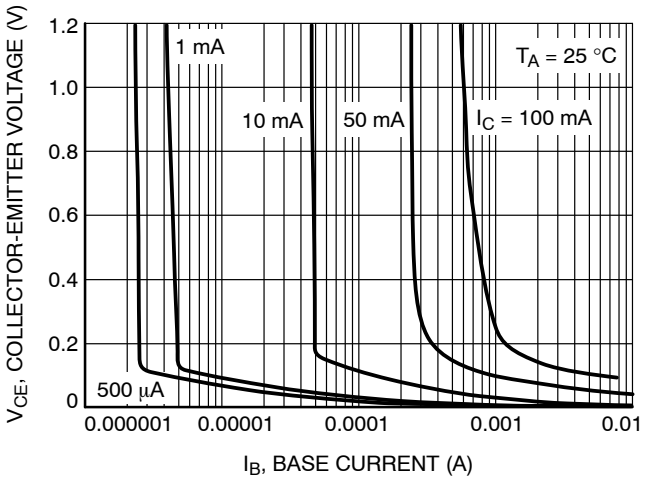

Figure 6. Collector Saturation Region

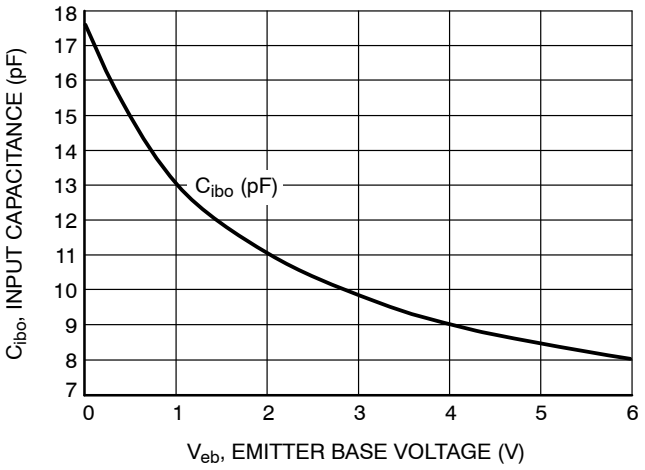

Figure 7. Input Capacitance

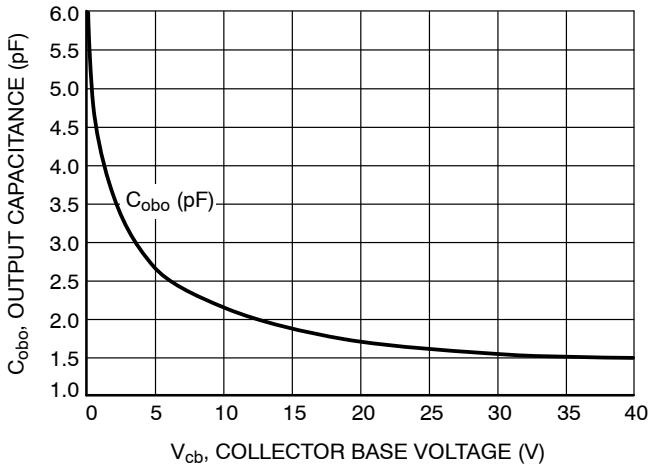

Figure 8. Output Capacitance

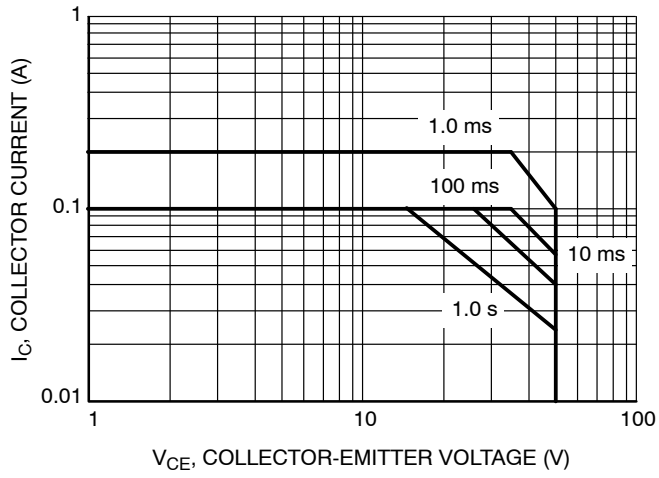

Figure 9. Safe Operating Area

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ORDERING INFORMATION

Device	Package	Shipping†
MSD601-RT1G	SC-59 (Pb-Free)	3000 / Tape & Reel
NSVMSD601-RT1G	SC-59 (Pb-Free)	3000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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REVISION HISTORY

Revision	Description of Changes	Date
11	Adding characteristics curves	3/26/2026

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

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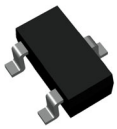
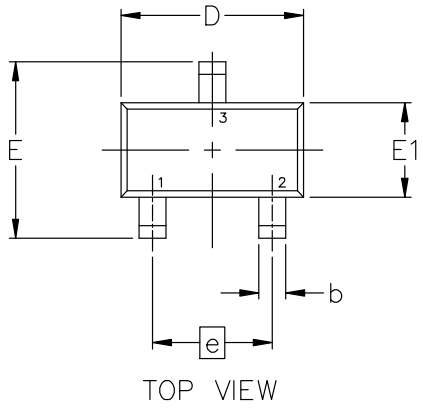
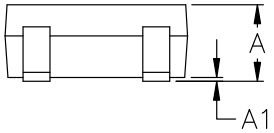


SC−59−3 2.90x1.50x1.15, 1.90P
CASE 318D
ISSUE J

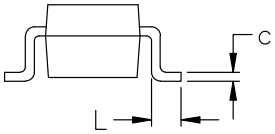
DATE 15 FEB 2024



TOP VIEW



SIDE VIEW

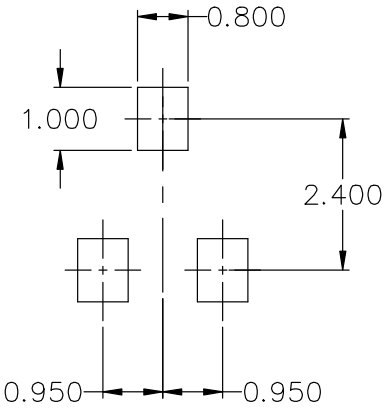


END VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS.

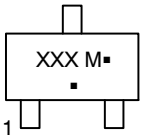
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.00	1.15	1.30
A1	0.01	0.06	0.10
b	0.35	0.43	0.50
c	0.09	0.14	0.18
D	2.70	2.90	3.10
E	2.50	2.80	3.00
E1	1.30	1.50	1.70
e	1.90 BSC		
L	0.20	0.40	0.60



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package*

(*Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. N.C.
3. ANODE

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE/CATHODE

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DESCRIPTION:	**SC−59−3 2.90x1.50x1.15, 1.90P**		**PAGE 1 OF 1**

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